Lehrstühle und Professuren

Autor(en) des Beitrags: Felgentreff, Tilmann; Olbrich, Gerhard R.; Russer, Peter

Titel des Beitrags: Noise Parameter Modeling of HEMTs with Resistor Temperature Noise Sources

Abstract: We present a new model to describe the millimeter wave noise performance of MESFETs and HEMTs. The model is used to extrapolate the noise parameters in frequency range and to describe the noise behaviour over a wide range of bias points. The model is based on three uncorrelated noise sources located at the intrinsic transistor, which are assumed to show white spectral behaviour. The parameters of the model are determined from noise parameter measurements. The noise parameter extraction technique is straightforward and based on circuit simulation programs. The model is applied to several pseudomorphic and conventional HEMT structures and results are compared with data obtained from other models.

Stichworte: circuit simulation programs, equivalent circuits, HEMTs, high electron mobility transistors, MESFETs, millimeter wave noise performance, MM-wave FETs, noise parameter extraction technique, noise parameter modeling, pseudomorphic structures, resistor temperature noise sources, Schottky gate field effect transistors, semiconductor device models, semiconductor device noise, solid-state microwave devices, thermal noise, white noise, white spectral behaviour

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